Second Mixer IF for digital mobile phones BH4128FV

The BH4128FV is an IC equipped with internal second mixer and IF amplifier circuits, developed for use with digital portable telephones.

Applications

Digital mobile phones

●Features

- 1) Equipped with internal mixer, IF, and RSSI circuits.
- 2) Can be operated at mixer input frequencies ranging from 10MHz to 200MHz.
- 3) IF amplifier gain is 100 dB.
- 4) Equipped with a battery power saving function.

●Absolute maximum ratings (Ta=25℃, for measurement circuit)

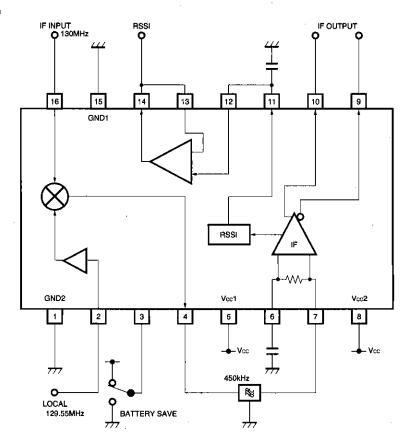
Parameter	Symbol Limits		Unit	
Power supply voltage	Vcc	7.0	V	
Power dissipation	Pd	350 *	mW ℃	
Storage temperature	Tstg	− 55∼+125		

^{*1} Reduced by 3.5mW for each increase In Ta of 1℃ over 25℃.

■Recommended operating conditions (Ta=25°C, for measurement circuit)

Parameter	Symbol	Limits	Unit	
Operating voltage	Vcc	2.3~5.5	V	
Operating temperature	Tpor	-40~ + 85	င	

Block diagram



●Pin descriptions

Pin No.	Function	Internal peripheral circuit	DC voltage (V)
1	GND pin 2	GND for MIX stage	GND
2	Local oscillation input pin Input from external oscillator	Voc 15p 15p Voc BIAS 2.4k	_
3	Battery save pin "Pin3 voltage" ≦0.2V: Battery save 2V≦ "Pin3 voltage" ≦Vcc: Active	3 50k W	-
4	Mixer output pin Connect ceramic filter Output impedance: 1 kΩ	900 W	Vcc-1.6
5	Vcc pin 1	Vcc for MIX stage and IF amplifier early stage	Vcc

IFs for radio communications

Pin No.	Function	Internal peripheral circuit	DC voltage (V)
6	IF amplifier bypass pin Connect capacitor	Vcc 15k ≥ 500 000 000 000 000 000 000 000 000 0	Vcc-0.6
7	IF amplifier input pin Connect ceramic filter Output impedance: 1 kΩ		Vcc-0.6
8	Vcc pin 2	Vcc for IF later stage	Vcc
9, 10	IF amplifier output pin Pins 9 and 10 are opposite-phase output	200 B or 10	Vcc-1.2
11	RSSI output pin Connect capacitor	50k ₹	0.15

Function	Internal peripheral circuit	DC voltage (V)
Buffer amplifier non-reversed input pin	V _{cc}	
Buffer amplifier reversed input pin		_
Buffer amplifier output pin	200 14	_
GND pin 1	GND for IF stage and RSSI circuit	GND
Mixer input pin Connect first IF signal from DC cutoff	1.6k	1.2
	Buffer amplifier non-reversed input pin Buffer amplifier reversed input pin Buffer amplifier output pin GND pin 1 Mixer input pin Connect first IF signal from DC	Buffer amplifier non-reversed input pin Buffer amplifier reversed input pin Buffer amplifier output pin GND pin 1 GND for IF stage and RSSI circuit Mixer input pin Connect first IF signal from DC cutoff

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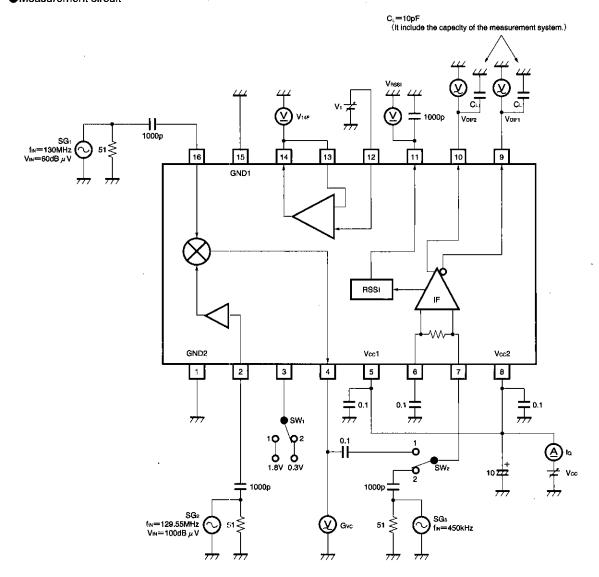
Electrical characteristics (Unless otherwise noted, Ta=25°C, Vcc=3.0V;
 Signal source: fin (MIX)=130MHz
 fin (LO)=129.55MHz, 100dB μV

all AC levels are end display)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Quiescent current	la	_	3.0	3.9	mA	V _{IN (LO)} =100dB μ V
Battery save quiescent current	la (BS)	. –	0	5	μΑ	
P-H	V тн-н	2	_	Vcc	V	Active
Battery save input voltage	V _{TH} -L	GND	_	0.2	V	Battery save
MIX - oscillator unit	—- ···le				1	
Mixer operating frequency	fмix	10	130	200	MHz	
Mixer conversion gain	Gvc	8.5	12.5	16.5	dB	$V_{IN (MIX)} = 60dB \mu V, RL = 1k\Omega$
-1 dB compression output level	Vом	_	101	_	dB μV	
3rd intercept point	IP ₃	_	115	_	dB μV	f1=130.05MHz, f2=130.10MHz
Noise index	NF	_	8.5	_	dB	LC matching input
Mixer input admittance	YIN (MIX)	_	0.38+j2.75	_	mS	f=130MHz
Mixer output resistance	Во (міх)	_	1	_	kΩ	
Local input level	Vin (LO)	95	100	105	dB μV	
Local input admittance	YIN (LO)	_	0.25+j3.65	_	mS	f=130MHz
IF unit					'	
IF operating frequency	fir	350	_	500	kHz	
IF amplifier gain	Gv	_	100	-	dB	
IF input resistance	Rin (if)		1	_	kΩ	
IF output level	Voif	0.7	1	1.3	V _{P-P}	V _{IN (IF)} =80dB μV
IF output duty ratio	DR	45	50	55	%	V _{IN (IF)} =80dB μV, C _L =10pF
RSSI unit	•					,
Output voltage 1	Vassii		0.15	0.4	ν	No Input
Output voltage 2	V _{RSSI2}	1.0	1.2	1.4	V	V _{IN (IF)} =65dB μV
Output voltage 3	Vassis	1.8	2.0	2.2	V	V _{IN (IF)} =100dB μ V
Dynamic range	DR	_	85	_	dB	
Output resistance	Ro (RSSI)	40	50	60	kΩ	
Power ON rise time	Ton	_	140	_	μ \$0C	CL=1000pF, Vin (MIX)=60dB μV
Power OFF fall time	Toff	_	130	-	μSec	CL=1000pF, Vin (MIX)=60dB μ V
RSSI rise time	Tn	_	270	-	μsec	CL=1000pF, Vin (MIX)=60dB μ V
RSSI fall time	TF	_	220	_	μsec	C _L =1000pF, V _{IN (MIX)} =60dB μ V

O Not designed for radiation resistance.

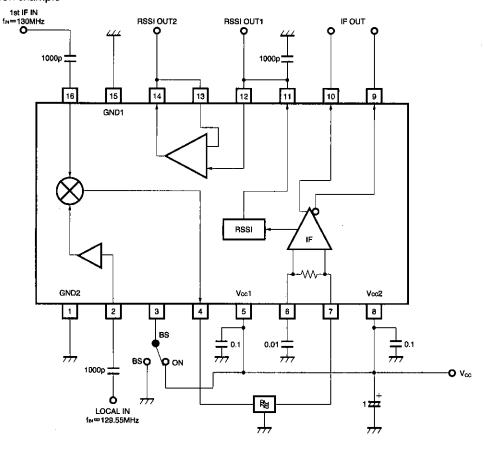
Measurement circuit



Unit Resistance : Ω Capacitor : μ F

Fig. 1

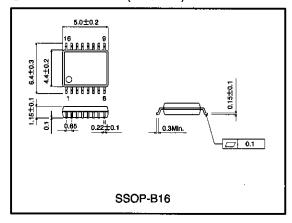
Application example



Unit Resistance : Ω Capacitor : μF

Fig. 2

●External dimensions (Units: mm)



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